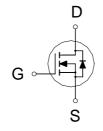
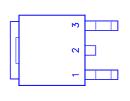
N-Channel Logic Level Enhancement Mode Field Effect Transistor

P0903BDG TO-252 (DPAK) Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	R _{DS(ON)}	I _D		
25	9.5m	50A		





1. GATE

2. DRAIN

3. SOURCE

ABSOLUTE MAXIMUM RATINGS (T_c = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST C	SYMBOL	LIMITS	UNITS	
Gate-Source Voltage		V_{GS}	±20	V
Continuous Dusin Coursest	T _C = 25 °C	,	50	
Continuous Drain Current	T _C = 100 °C	- I _D -	35	^
Pulsed Drain Current ¹	I _{DM}	200	A	
Avalanche Current		I _{AR}	40	
Avalanche Energy L = 0.1mH		E _{AS}	250	
Repetitive Avalanche Energy ²	L = 0.05mH	E _{AR}	8.6	— mJ
David Discipation	T _C = 25 °C	D	50	10/
Power Dissipation	T _C = 100 °C	$ P_D$ $-$	30	W
Operating Junction & Storage Temp	T_{j},T_{stg}	-55 to 150	00	
Lead Temperature (1/16" from case for	T _L	275	°C	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{ heta JC}$		2.5	
Junction-to-Ambient	$R_{ hetaJA}$		62.5	°C / W
Case-to-Heatsink	$R_{ heta CS}$	0.6		

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

DADAMETED	CVMDOL	TEGT CONDITIONS	LIMITS			
PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	25			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.6	3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 20V$			±250	nA
Zoro Coto Voltogo Proin Current	I _{DSS}	$V_{DS} = 20V$, $V_{GS} = 0V$			25	Δ.
Zero Gate Voltage Drain Current		$V_{DS} = 20V, V_{GS} = 0V, T_{C} = 125 ^{\circ}C$			250	μΑ

²Duty cycle ≤ 1%

NIKO-SEM

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On-State Drain Current ¹	I _{D(ON)}	$V_{DS} = 10V, V_{GS} = 10V$	50			Α		
Drain-Source On-State	-D(ON)	$V_{GS} = 4.5V, I_{D} = 20A$		11	16			
Resistance ¹	R _{DS(ON)}	$V_{GS} = 10V, I_D = 25A$		7.5	9.5	m		
Forward Transconductance ¹	g fs	$V_{DS} = 10V, I_{D} = 25A$		32		S		
DYNAMIC								
Input Capacitance	C_{iss}			1200	1800			
Output Capacitance	C _{oss}	$V_{GS} = 0V$, $V_{DS} = 15V$, $f = 1MHz$		600	1000	pF		
Reverse Transfer Capacitance	C _{rss}			350	500	1		
Total Gate Charge ²	Qg			25	50			
Gate-Source Charge ²	Q_{gs}	$V_{DS} = 10V, V_{GS} = 10V,$		15		nC		
Gate-Drain Charge ²	Q_{gd}	I _D = 25A		10				
Turn-On Delay Time ²	t _{d(on)}			6	16			
Rise Time ²	t _r	$V_{DS} = 15V, R_L = 1$		120	250	0		
Turn-Off Delay Time ²	$t_{d(off)}$	$I_D \cong 50A, \ V_{GS} = 10V, \ R_{GEN} = 24$		40	90	nS		
Fall Time ²	t _f			105	200			
SOURCE-DRAIN D	OODE RAT	INGS AND CHARACTERISTICS (T _C	= 25 °	C)				
Continuous Current	Is				50	۸		
Pulsed Current ³	I _{SM}				150	Α		
Forward Voltage ¹	V_{SD}	$I_S = 25A, V_{GS} = 0V$		0.9	1.3	V		
Reverse Recovery Time	t _{rr}			70		nS		
Peak Reverse Recovery Current	I _{RM(REC)}	$I_F = I_S$, $dI_F/dt = 100A / \mu S$		200		Α		
Reverse Recovery Charge	Q _{rr}			0.043		μС		

¹Pulse test : Pulse Width ≤ 300 μ sec, Duty Cycle ≤ 2%.

REMARK: THE PRODUCT MARKED WITH "P0903BDG", DATE CODE or LOT

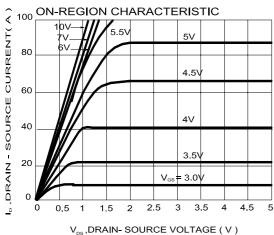
Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.

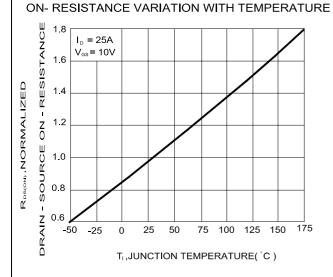
²Independent of operating temperature. ³Pulse width limited by maximum junction temperature.

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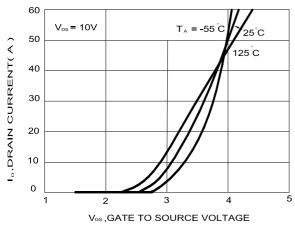
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TYPICAL CHARACTERISTICS

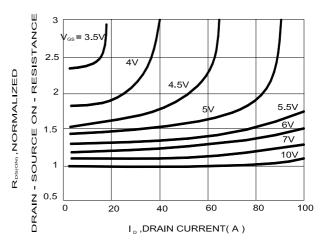




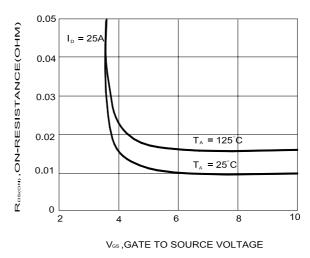
TRANSFER CHARACTERISTICS



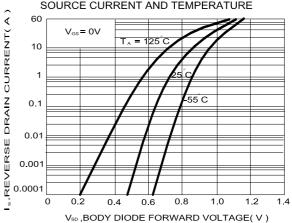
ON- RESISTANCE VARIATION WITH DRAIN CURRENT AND GATE



ON-RESISTANCE VARIATION WITH GATE-TO-SOYRCE VOLTAGE



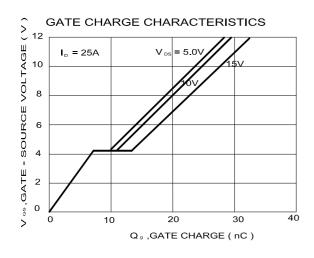
BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

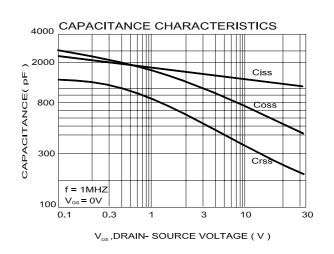


NIKO-SEM

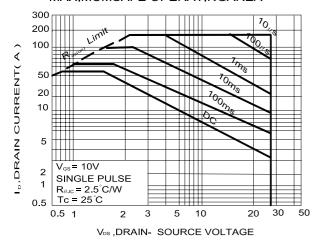
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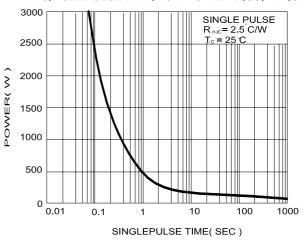




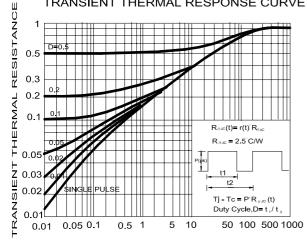
MAXIMUMSAFE OPERATINGAREA



SINGLEPULSE MAXIMUM POWER DISSIPATION



TRANSIENT THERMAL RESPONSE CURVE



t1, TIME(ms)

r 🖽 ,NORMALIZED EFFECTIVE

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
Dimension	Min.	Тур.	Max.	Dimension	Min.	Тур.	Max.
Α	9.35		10.4	Н	0.89		2.03
В	2.2		2.4	I	6.35		6.80
С	0.45		0.6	J	5.2		5.5
D	0.89		1.5	K	0.6		1
Е	0.45		0.69	L	0.5		0.9
F	0.03		0.23	М	3.96	4.57	5.18
G	5.2		6.2	N			

